



ON Semiconductor®

ON Semiconductor
DATA SHEET

N-Channel Silicon MOSFET

ECH8616 — General-Purpose Switching Device Applications**Features**

- Ultrahigh-speed switching.
- 4V drive.
- Composite type, facilitating high-density mounting.

Specifications**Absolute Maximum Ratings** at $T_a=25^{\circ}\text{C}$

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DS}		60	V
Gate-to-Source Voltage	V_{GS}		± 20	V
Drain Current (DC)	I_D		3	A
Drain Current (Pulse)	I_{DP}	$PW \leq 10\mu\text{s}$, duty cycle $\leq 1\%$	20	A
Allowable Power Dissipation	P_D	Mounted on a ceramic board (900mm ² ×0.8mm) 1unit	1.3	W
Total Dissipation	P_T	Mounted on a ceramic board (900mm ² ×0.8mm)	1.5	W
Channel Temperature	T_{ch}		150	$^{\circ}\text{C}$
Storage Temperature	T_{stg}		-55 to +150	$^{\circ}\text{C}$

Electrical Characteristics at $T_a=25^{\circ}\text{C}$

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D=1\text{mA}$, $V_{GS}=0$	60			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS}=60\text{V}$, $V_{GS}=0$			1	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 16\text{V}$, $V_{DS}=0$			± 10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS}=10\text{V}$, $I_D=1\text{mA}$	1.2		2.6	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS}=10\text{V}$, $I_D=1.5\text{A}$	2.2	3.8		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)1}$	$I_D=1.5\text{A}$, $V_{GS}=10\text{V}$		70	93	$\text{m}\Omega$
	$R_{DS(on)2}$	$I_D=0.5\text{A}$, $V_{GS}=4\text{V}$		92	133	$\text{m}\Omega$
Input Capacitance	C_{iss}	$V_{DS}=20\text{V}$, $f=1\text{MHz}$		560		pF
Output Capacitance	C_{oss}	$V_{DS}=20\text{V}$, $f=1\text{MHz}$		60		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS}=20\text{V}$, $f=1\text{MHz}$		41		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		11		ns
Rise Time	t_r	See specified Test Circuit.		11		ns
Turn-OFF Delay Time	$t_{d(off)}$	See specified Test Circuit.		61		ns
Fall Time	t_f	See specified Test Circuit.		32		ns

Marking : FJ

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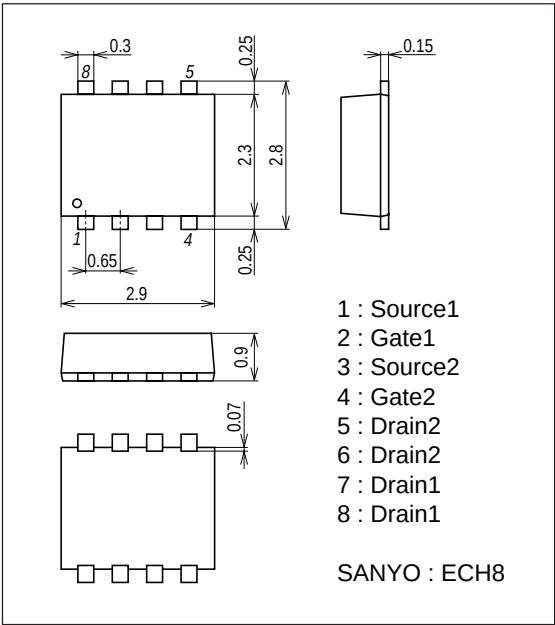
ECH8616

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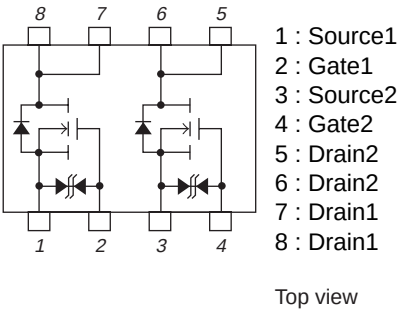
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Total Gate Charge	Qg	V _{DS} =30V, V _{GS} =10V, I _D =3A		12.8		nC
Gate-to-Source Charge	Qgs	V _{DS} =30V, V _{GS} =10V, I _D =3A		2.1		nC
Gate-to-Drain "Miller" Charge	Qgd	V _{DS} =30V, V _{GS} =10V, I _D =3A		2.7		nC
Diode Forward Voltage	V _{SD}	I _S =3A, V _{GS} =0		0.81	1.2	V

Package Dimensions

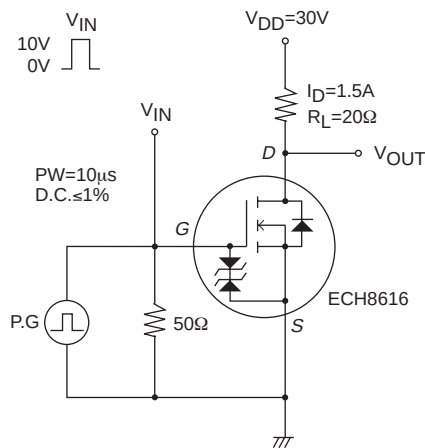
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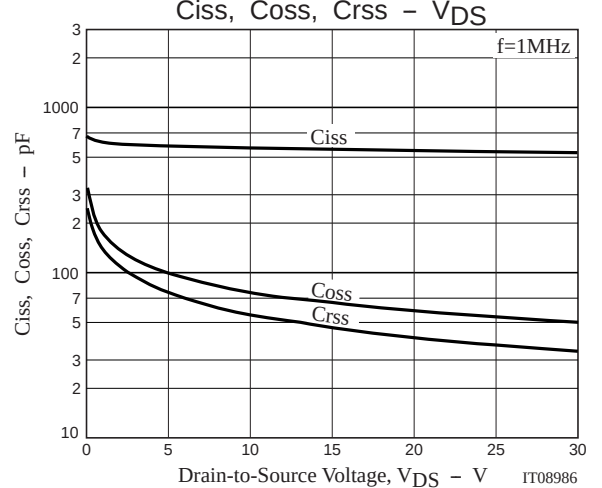
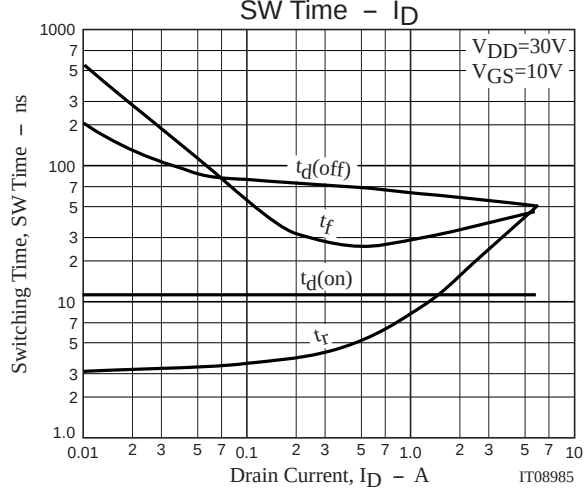
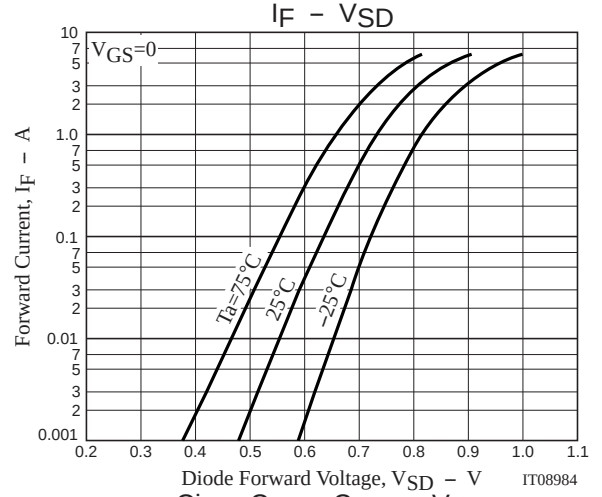
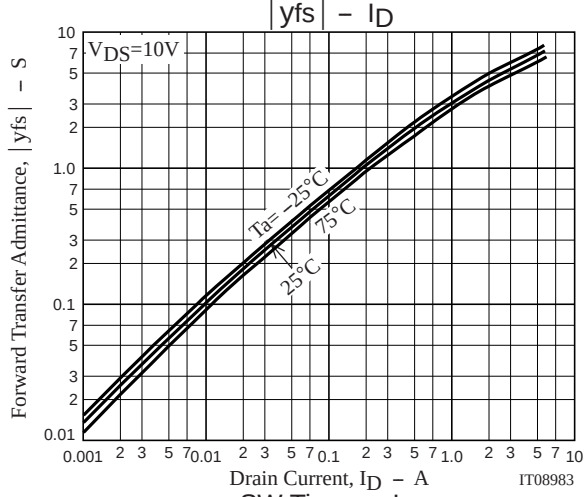
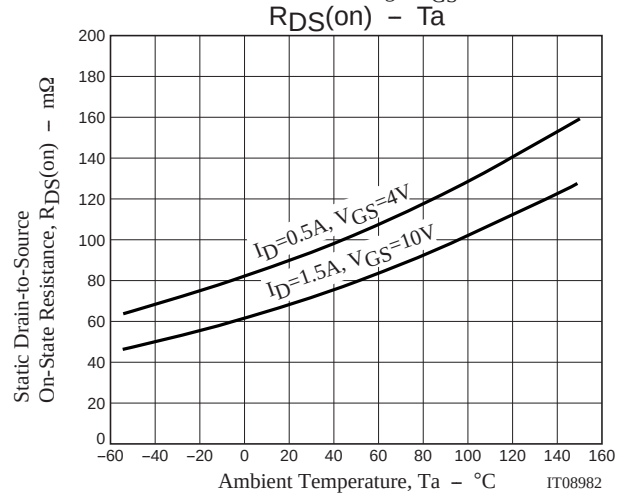
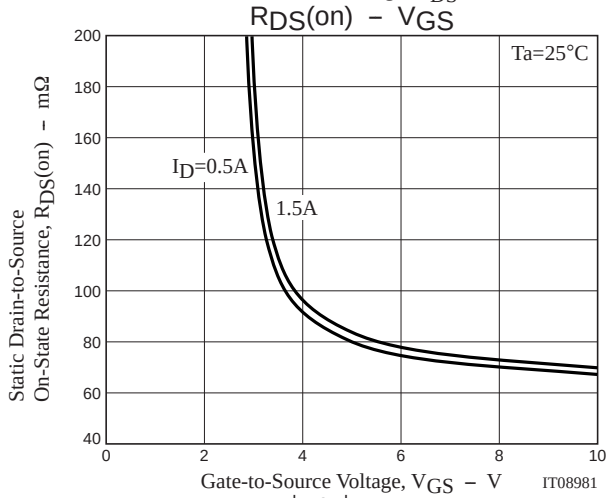
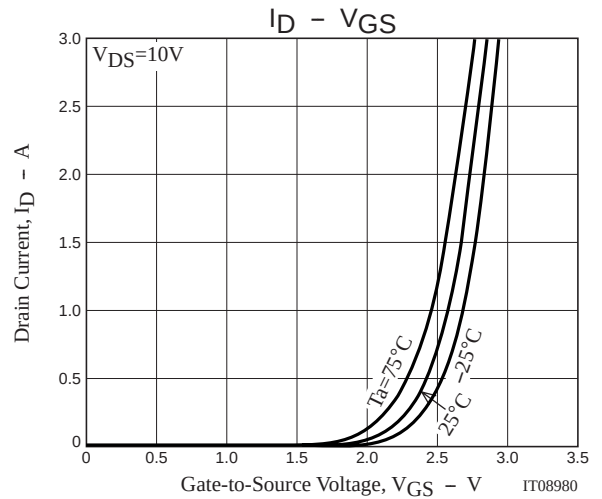
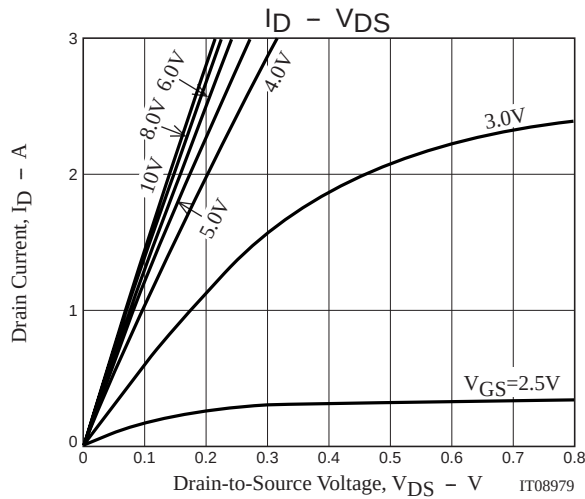


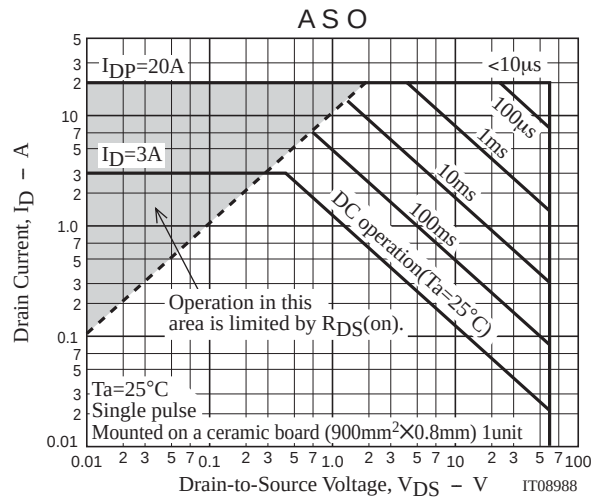
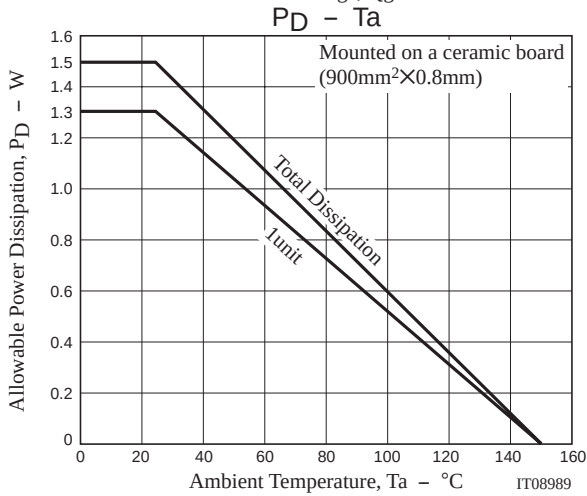
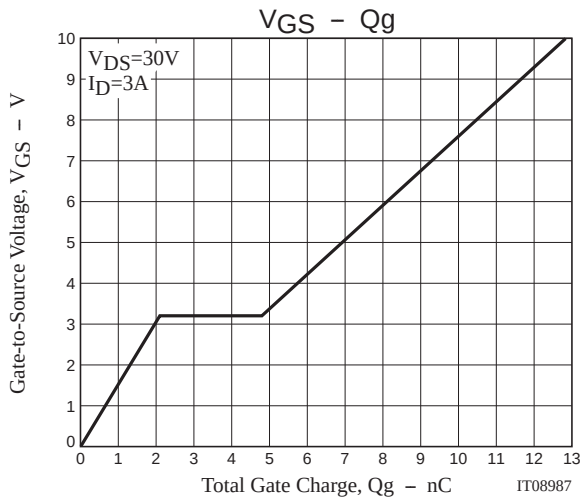
Electrical Connection



Switching Time Test Circuit







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